

3DG101, 3DG110, 3DG111



NPN Silicon High Frequency Low Power Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications						
			3DG101		3DG110			3DG111	
			A	B	C	D	E	F	Test Condition
C-B Breakdown Voltage	V _{(BR)CBO}	V	20	30	40	20	30	40	I _c =0.1mA
C-E Breakdown Voltage	V _{(BR)CEO}	V	15	20	30	15	20	30	
E-Base Breakdown Voltage	V _{(BR)EBO}	V	≥4 (I _E =0.1mA)			≥4 (I _E =0.1mA)			≥4 (I _E =0.1mA)
Total Dissipation	P _{tot}	mW	100 (T _a =25°C)			300 (T _a =25°C)			300 (T _a =25°C)
Max. Collector Current	I _{CM}	mA	20			50			50
Junction Temperature	T _{jm}	°C	175						
Storage Temperature	T _{stg}	°C	-55~+175						
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	0.35 (I _C =10mA, I _B =1mA)			1.0 (I _C =10mA, I _B =1mA)			0.35 (I _C =10mA, I _B =1mA)
Base- Emitter Saturation Voltage Drop	V _{BE(sat)}	V	1.0 (I _C =10mA, I _B =1mA)						
C-B Leakage Current	I _{CBO}	uA	0.01(V _{CB} =10V)			0.1(V _{CB} =10V)			
C-E Leakage Current	I _{CEO}	uA	0.01(V _{CE} =10V)			0.1(V _{CE} =10V)			
E-B Leakage Current	I _{EBO}	uA	0.01(V _{EB} =1.0V)			0.1(V _{EB} =1.0V)		0.1(V _{EB} =1.5V)	
DC Current Gain	h _{FE}		25~270 (V _{CE} =10V, I _C =0.5mA)			25~270 (V _{CE} =10V, I _C =10mA)			
Transition frequency	f _T	MHz	A~C:150,D~F:300 (V _{CE} =10V, I _C =10mA, f=100MHz)						

h_{FE} Colored:

Color	Orange	Yellow	Green	Blue	Purple	Gray
h _{FE}	25~40	40~55	55~80	80~120	120~180	180~270

Outline and Dimensions: